

LT9325E

■ Absolute Maximum Ratings *1

(Ta=25°C)

Parameter	Symbol	LT9325E				Unit
*2 Power dissipation	P	336				mW
Continuous forward current	I _F	60				mA
*3 Peak forward current	I _{FM}	100				mA
Derating factor	DC	—	1.09			mA/°C
	Pulse	—	1.82			mA/°C
Reverse voltage	V _R	5				V
Operating temperature	T _{opr}	-20 to +70				°C
Storage temperature	T _{stg}	-30 to +80				°C
*4 Soldering temperature	T _{sol}	260 (within 5 seconds)				°C

*1 Per chip

*2 Per lamp : 2 chips

*3 Duty ratio = 1/10, Pulse width = 0.1ms

*4 At the position of 4.4 mm from (A) level of outline dimensions

4

LT9325E (Yellow-green)

■ **Electro-optical** Characteristics *1

(Ta=25°C)

Parameter	Symbol	Model No.	Conditions	MIN.	TYP.	MAX	Unit
Forward voltage	V_F	LT9325E	$I_F = 40\text{mA}$	—	2.2	2.8	V
*5 Luminous intensity	I_V	LT9325E	$I_F = 40\text{mA}$	10	30	—	mcd
Peak emission wavelength	λ_p	LT9325E	$I_F = 40\text{mA}$	—	565	—	nm
Spectrum radiation bandwidth	$\Delta\lambda$	LT9325E	$I_F = 40\text{mA}$	—	30	—	nm
Reverse current	I_R	LT9325E	$V_R = 4\text{V}$	—	—	10	μA
Response frequency	f_c	LT9325E	—	—	4	—	MHz

*1 Per chip

*5 Per lamp : 2 chips

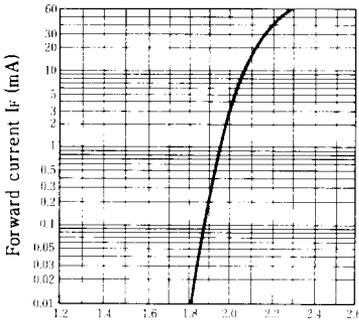
Effective area : 17.0 X 30.0mm

Tolerance : $\pm 30\%$

■ Characteristics Diagrams

Forward Current vs. Forward Voltage

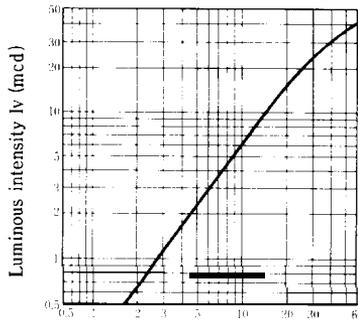
(Ta = 25°C)



Forward voltage V_F (V)

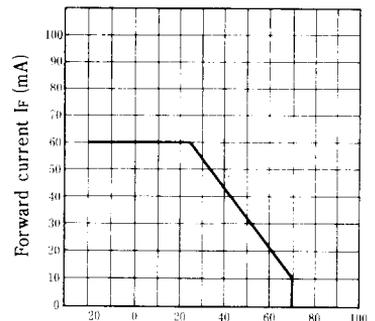
Luminous Intensity vs. Forward Current

(Ta = 25°C)



Forward current I_F (mA)

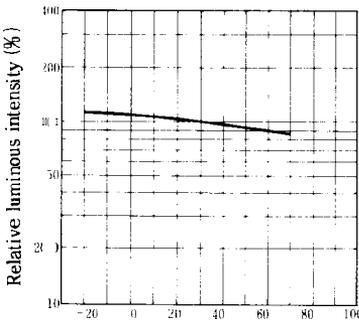
Forward Current Derating Curve



Ambient temperature T_a (°C)

Relative Luminous Intensity vs. Ambient Temperature

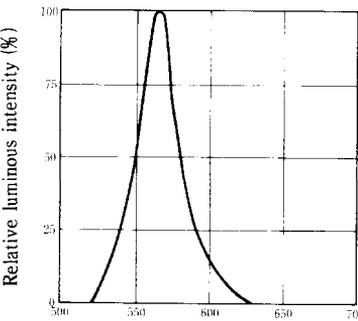
($I_F = 40\text{mA}$)



Ambient temperature T_a (°C)

Spectrum Distribution

(Ta = 25°C)



Wavelength λ (nm)